BLF8G20LS-400PV; BLF8G20LS-400PGV Power LDMOS transistor

AMPLEON

Rev. 5 — 1 September 2015

Product data sheet

Product profile

1.1 General description

400 W LDMOS power transistor with improved video bandwidth for base station applications at frequencies from 1805 MHz to 1995 MHz.

Table 1. Typical performance

Typical RF performance at T_{case} = 25 °C in a common source class-AB production test circuit, tested on straight lead device.

Test signal	f	I _{Dq}	V _{DS}	P _{L(AV)}	Gp	η_D	ACPR _{5M}
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	1805 to 1995	3400	28	95	19	28	-33 <u>[1]</u>

^[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 7.5 dB at 0.01 % probability on CCDF; carrier spacing = 5 MHz; f_1 = 1807.5 MHz; f_2 = 1812.5 MHz; f_3 = 1872.5 MHz; f_4 = 1877.5 MHz.

1.2 Features and benefits

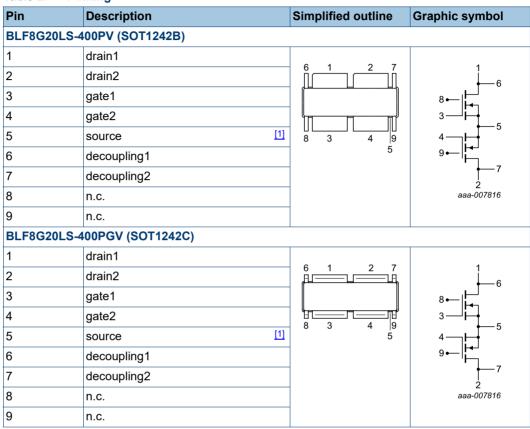
- Decoupling leads to enable improved Video BandWidth (VBW) (120 MHz typical)
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Designed for broadband operation
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Design optimized for gull-wing
- Excellent ruggedness
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

RF power amplifiers for base stations and multi carrier applications in the 1805 MHz to 1995 MHz frequency range

2. Pinning information

Table 2. Pinning



^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	Package				
	Name	Description	Version			
BLF8G20LS-400PV	-	earless flanged ceramic package; 8 leads	SOT1242B			
BLF8G20LS-400PGV	-	earless flanged ceramic package; 8 leads	SOT1242C			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	$T_{case} = 80 ^{\circ}C; P_{L} = 80 W$	0.23	K/W

6. Characteristics

Table 6. DC characteristics

 T_i = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 3.0 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 300 mA	1.5	1.9	2.3	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	3.0	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$		51.5	-	Α
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	300	nA
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 15 A	-	20.6	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 10.5 \text{ A}$	-	0.055	-	Ω

Table 7. RF characteristics

Test signal: 2-carrier W-CDMA; PAR = 7.5 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1-64 DPCH; f_1 = 1807.5 MHz; f_2 = 1812.5 MHz; f_3 = 1872.5 MHz; f_4 = 1877.5 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 3400 mA; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit, tested on straight lead device.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _{L(AV)} = 95 W	17.8	19	-	dB
RLin	input return loss	P _{L(AV)} = 95 W	-	-12	-6	dB
η_{D}	drain efficiency	P _{L(AV)} = 95 W	24	28	-	%
ACPR _{5M}	adjacent channel power ratio (5 MHz)	P _{L(AV)} = 95 W	-	-33	-28	dBc

7. Test information

7.1 Ruggedness in class-AB operation

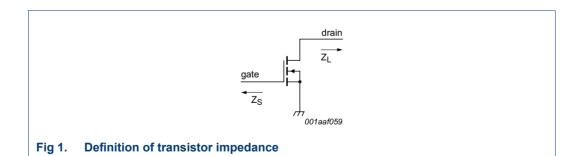
The BLF8G20LS-400PV and BLF8G20LS-400PGV are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 3300 mA; 2-carrier W-CDMA signal; P_{L} = 200 W; f_{c} = 1800 MHz; 5 MHz spacing, 46 % clipping.

7.2 Impedance information

Table 8. Typical impedance for the top-half of the push-pull package Measured load-pull data; $I_{Dq} = 1800 \text{ mA}$; $V_{DS} = 28 \text{ V}$; $T_{case} = 25 ^{\circ}\text{C}$, water cooled.

modearou reau pan data, ibq	see, 103 = 1, 10ase = 0	,
f	Z _S [1]	Z _L [1]
(MHz)	(Ω)	(Ω)
BLF8G20LS-400PV (straight le	ad)	
1800	4.1 – j4.66	4.1 – j4.5
1840	5.2 – j3.6	4.4 – j4.4
1880	4.6 – j1.45	4.85 – j4.25
1930	2.8 – j0.3	4.5 – j4.3
1960	2.1 – j0.5	5.5 – j3.5
1990	1.56 – j0.6	5.5 – j3.4
BLF8G20LS-400PGV (gull-win	g)	
1800	3.7 – j7.6	4.2 – j6.8
1840	4.34 – j6.1	4.4 – j6.7
1880	4.75 – j5.2	4 – j6.4
1930	3.17 – j3.4	4.6 – j6.5
1960	2 – j3.05	5.8 – j5.5
1990	2.5 – j2.6	5.8- j5.7

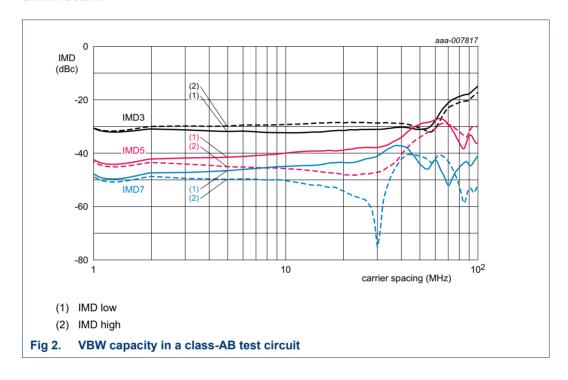
[1] Z_S and Z_L defined in Figure 1.



7.3 VBW in class-AB operation

The BLF8G20LS-400PV and BLF8G20LS-400PGV have a video bandwidth of 120 MHz (typical) when measured in a class-AB test circuit operating in the 1800 MHz to 1880 MHz frequency band for V_{DS} = 28 V and I_{Dq} = 3.3 A, where the VBW is defined as the location of the resonance in the base-band impedance measurement obtained using a low-frequency probe.

The VBW measurement based on the 2-tone IMD test as a function of carrier spacing is shown below.



7.4 Test circuit

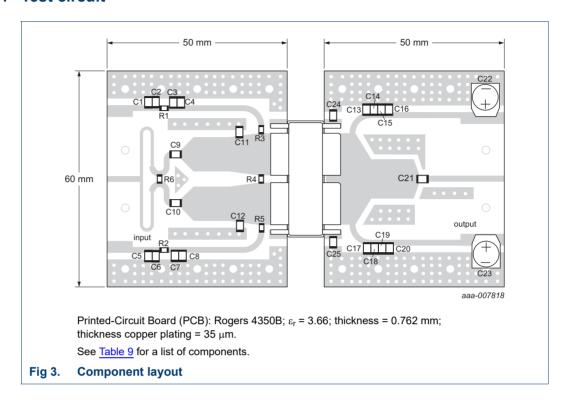


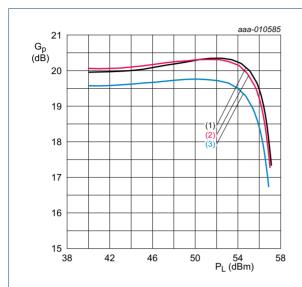
Table 9. List of components

See Figure 3 for component layout.

Component	Description	Value	Remarks
C1, C5, C16, C20	multilayer ceramic chip capacitor	10 μF, 50 V	Murata, SMD 2220
C2, C6, C15, C19, C24, C25	multilayer ceramic chip capacitor	4.7 μF, 50 V	Murata
C3, C7, C14, C18	multilayer ceramic chip capacitor	1 nF	ATC100B
C4, C8, C9, C10, C13, C17, C21	multilayer ceramic chip capacitor	24 pF	ATC100B
C11, C12	multilayer ceramic chip capacitor	100 pF	ATC100B
C22, C23	electrolytic capacitor	2200 μF, 63 V	
R1, R2	resistor	10 Ω	SMD 1206
R3, R5	resistor	5.1 Ω	SMD 1206
R4	resistor	33 Ω	SMD 1206
R6	resistor	100 Ω	SMD 1206

7.5 Graphical data

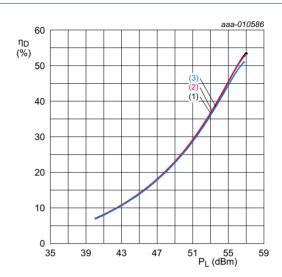
7.5.1 Pulsed CW



 V_{DS} = 28 V; I_{Dq} = 3400 mA; t_p = 100 μ s; δ = 10 %.

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

Fig 4. Power gain as a function of output power; typical values

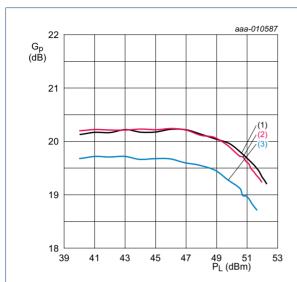


 V_{DS} = 28 V; I_{Dq} = 3400 mA; t_p = 100 μ s; δ = 10 %.

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

Fig 5. Drain efficiency as a function of output power; typical values

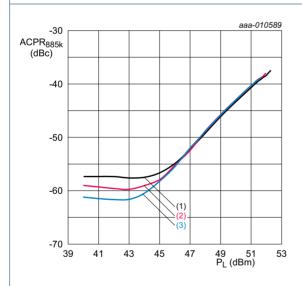
7.5.2 IS-95



 $V_{DS} = 28 \text{ V}; I_{Dq} = 3400 \text{ mA}.$

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

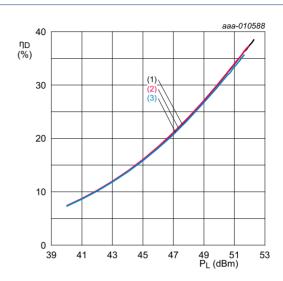
Fig 6. Power gain as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 3400 \text{ mA}.$

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

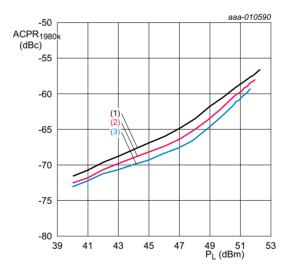
Fig 8. Adjacent channel power ratio (885 kHz) as a function of output power; typical values



 $V_{DS} = 28 \text{ V}$; $I_{Da} = 3400 \text{ mA}$.

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

Fig 7. Drain efficiency as a function of output power; typical values

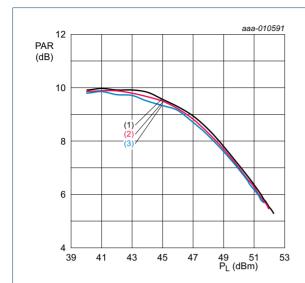


 $V_{DS} = 28 \text{ V}; I_{Dq} = 3400 \text{ mA}.$

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

Fig 9. Adjacent channel power ratio (1980 kHz) as a function of output power; typical values

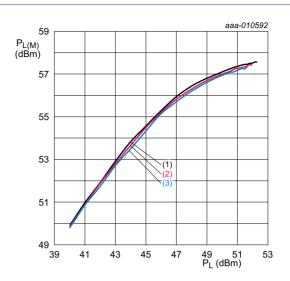
Power LDMOS transistor



 $V_{DS} = 28 \text{ V}; I_{Dq} = 3400 \text{ mA}.$

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

Fig 10. Peak-to-average ratio as a function of output power; typical values

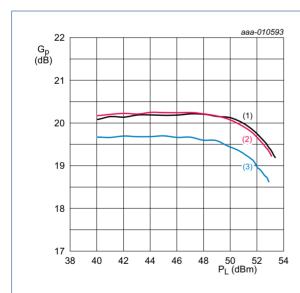


 $V_{DS} = 28 \text{ V}; I_{Dq} = 3400 \text{ mA}.$

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

Fig 11. Peak output power as a function of output power; typical values

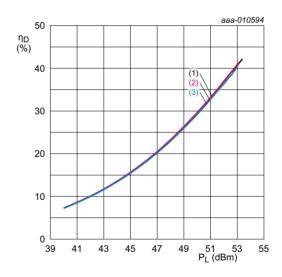
7.5.3 1-Carrier W-CDMA



 $V_{DS} = 28 \text{ V}; I_{Dq} = 3400 \text{ mA}.$

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

Fig 12. Power gain as a function of output power; typical values

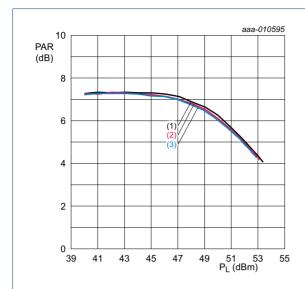


 V_{DS} = 28 V; I_{Dq} = 3400 mA.

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

Fig 13. Drain efficiency as a function of output power; typical values

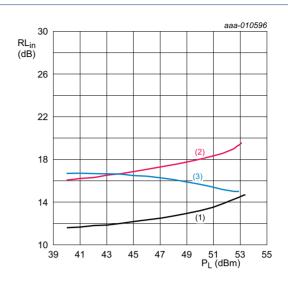
Power LDMOS transistor



 $V_{DS} = 28 \text{ V}; I_{Dq} = 3400 \text{ mA}.$

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

Fig 14. Peak-to-average ratio as a function of output power; typical values

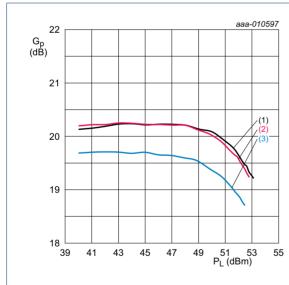


 $V_{DS} = 28 \text{ V}; I_{Dq} = 3400 \text{ mA}.$

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

Fig 15. Input return loss as a function of output power; typical values

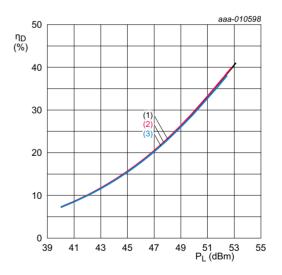
7.5.4 2-Carrier W-CDMA



 V_{DS} = 28 V; I_{Dq} = 3400 mA.

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

Fig 16. Power gain as a function of output power; typical values

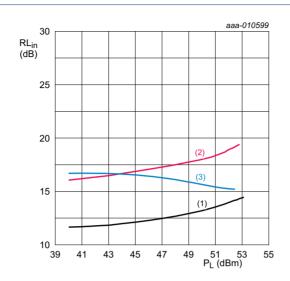


 $V_{DS} = 28 \text{ V}; I_{Dq} = 3400 \text{ mA}.$

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

Fig 17. Drain efficiency as a function of output power; typical values

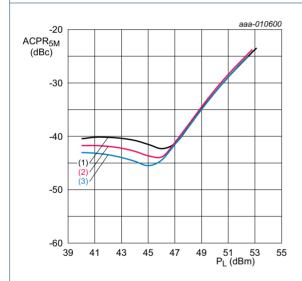
Power LDMOS transistor



 $V_{DS} = 28 \text{ V}; I_{Dq} = 3400 \text{ mA}.$

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

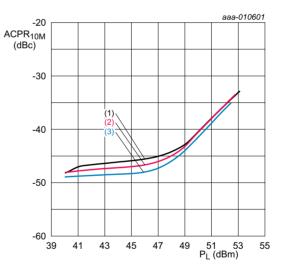
Fig 18. Input return loss as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 3400 mA.

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

Fig 19. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 3400 mA.

- (1) f = 1805 MHz
- (2) f = 1840 MHz
- (3) f = 1880 MHz

Fig 20. Adjacent channel power ratio (10 MHz) as a function of output power; typical values

8. Package outline

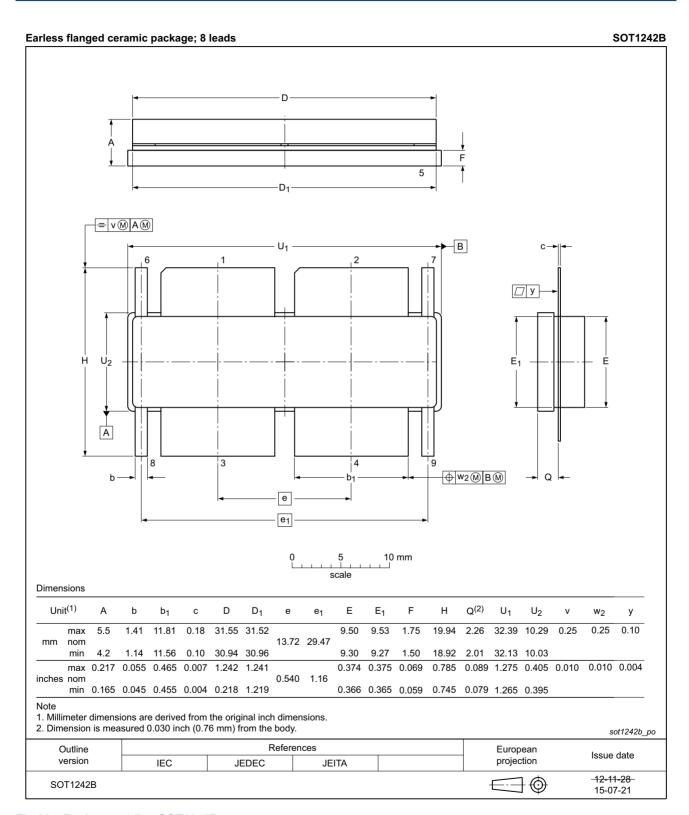


Fig 21. Package outline SOT1242B

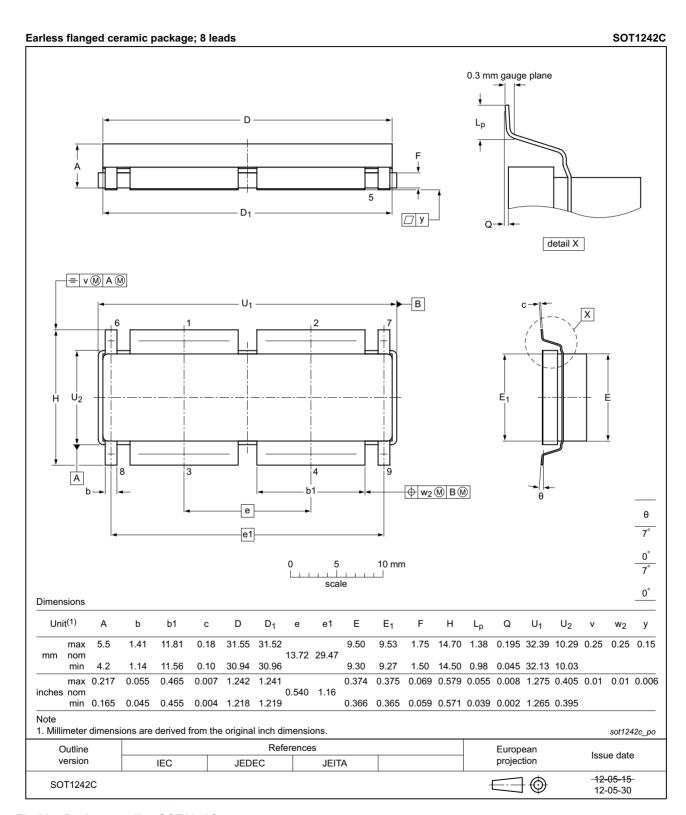


Fig 22. Package outline SOT1242C

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 10. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical Channel
ESD	ElectroStatic Discharge
IMD	InterModulation Distortion
IS-95	Interim Standard 95
LDMOS	Laterally Diffused Metal Oxide Semiconductor
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLF8G20LS-400PV_LS-400PGV#5	20150901	Product data sheet		BLF8G20LS-400PV _LS-400PGV v.4	
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of Ampleon. 				
	 Legal texts 	have been adapted to the	new company nar	ne where appropriate.	
BLF8G20LS-400PV_LS-400PGV v.4	20150728	Product data sheet	-	BLF8G20LS-400PV _LS-400PGV v.3	
BLF8G20LS-400PV_LS-400PGV v.3	20140603	Product data sheet	-	BLF8G20LS-400PV _LS-400PGV v.2	
BLF8G20LS-400PV_LS-400PGV v.2	20130625	Product data sheet	-	BLF8G20LS-400PV _LS-400PGV v.1	
BLF8G20LS-400PV_LS-400PGV v.1	20130606	Preliminary data sheet	-	-	

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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Power LDMOS transistor

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BLF8G20LS-400P(G)V

Power LDMOS transistor

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.